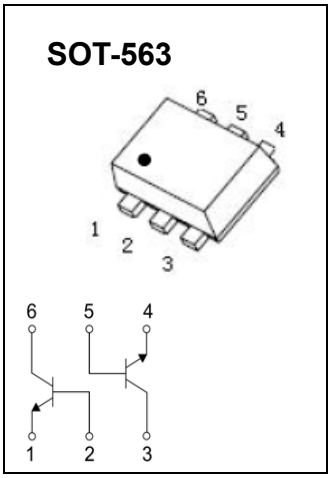
Plastic-Encapsulate Transistors

DUAL TRANSISTOR(NPN+NPN)



FEATURES

- Epitaxial Die Construction
- Complementary PNP Type Available (BC856BV)
- Ultra-Small Surface Mount Package

Marking: 4BV

MAXIMUM RATINGS(T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	0.15	W
$R_{\theta}JA$	Thermal Resistance. Junction to Ambient Air	833	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55 ~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=10mA,I_B=0	65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=70V,I_E=0			100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			100	nA
DC current gain	$h_{FE(1)}$	V_{CE}=5V,I_C=2mA	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10mA,I_B=0.5mA I_C=100mA,I_B=5mA			250 500	mV
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=100mA,I_B=5mA			1.1	V
Transition frequency	f_T	V_{CE}=5V,I_C=10mA,f=100MHz	100			MHz
Output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz			1.5	pF

Typical Characteristics